Product data sheet

1. General description

Planar passivated SCR with sensitive gate in a SOT223 surface mountable plastic package. This SCR is designed to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Direct triggering from low power drivers and logic ICs
- Surface mountable package

3. Applications

- · Circuit breakers
- RCD/GFI/LCCB applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; T _{sp} ≤ 112 °C; <u>Fig. 1</u>	-	-	0.63	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{sp} \le 112 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	-	1	А
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	-	8	Α
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	-	-	9	Α
Tj	junction temperature		-	-	125	°C
Static charact	eristics				,	
I _{GT}	gate trigger current	V_D = 12 V; I_T = 10 mA; T_j = 25 °C; Fig. 9	20	50	200	μA
Dynamic char	acteristics					_
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GK} = 1 kΩ; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 14	500	800	-	V/µs

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V_{DM} = 402 V; T_{j} = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	-	25	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	4	А - К
2	Α	anode		G sym037
3	G	gate		symosi
4	mb	mb; connected to anode	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

6. Ordering informat on

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
DT4C0CIM	0.07000	BT168GW ,115	Reel	1000	007000	40 M 0000
BT168GW	W SOT223 BT168GW ,135	Reel	4000	SOT223	16-Mar-2006	

Orderable part number	Marking codes				
	Assembly factory: d	Assembly factory: L			
BT168GW ,115	Jdxxx BT168G	JLxxx BT168G			
BT168GW ,135	Jdxxx BT168G	-			

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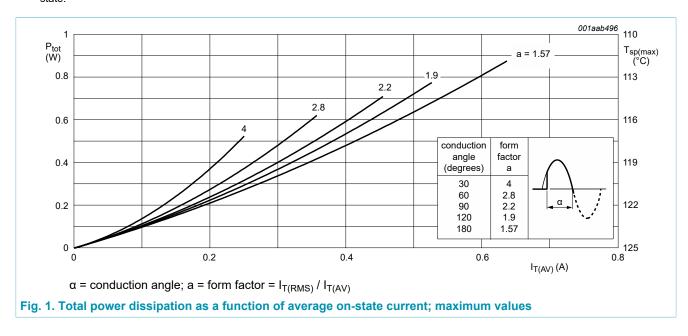
7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		[1]	-	600	V
V_{RRM}	repetitive peak reverse voltage			-	600	V
I _{T(AV)}	average on-state current	half sine wave; T _{sp} ≤ 112 °C; <u>Fig. 1</u>		-	0.63	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{sp} ≤ 112 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	1	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		-	8	А
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		-	9	Α
I ² t	I ² t for fusing	t _p = 10 ms; SIN		-	0.32	A²s
dl _T /dt	rate of rise of on-state current	$I_T = 2 \text{ A}$; $I_G = 10 \text{ mA}$; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$		-	50	A/µs
I _{GM}	peak gate current			-	1	Α
V_{RGM}	peak reverse gate voltage			-	5	V
P_{GM}	peak gate power			-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.1	W
T _{stg}	storage temperature			-40	150	°C
Tj	junction temperature			-	125	°C

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the thyristor may switch to the onstate.



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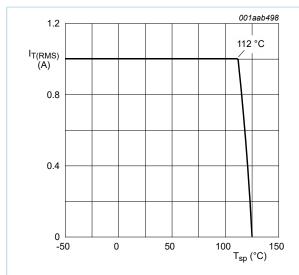


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

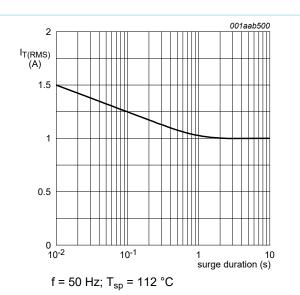


Fig. 3. RMS on-state current as a function of surge duration; maximum values

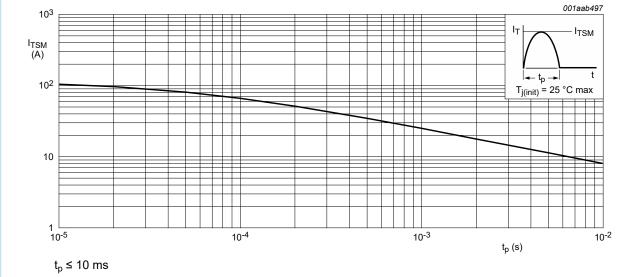


Fig. 4. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

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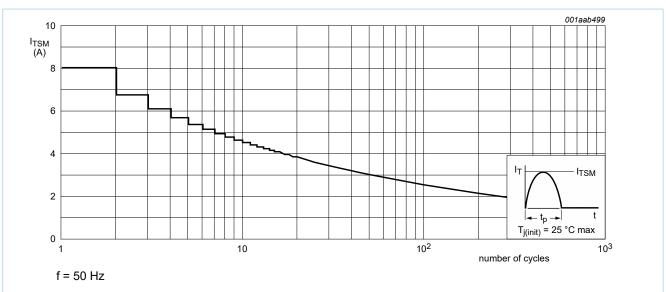


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	Fig. 6	-	-	15	K/W
uig-a)	thermal resistance from junction to	printed circuit board mounted; minimum footprint; Fig. 7	-	156	-	K/W
	ambient free air	printed circuit board mounted; pad area; Fig. 8	-	70	-	K/W

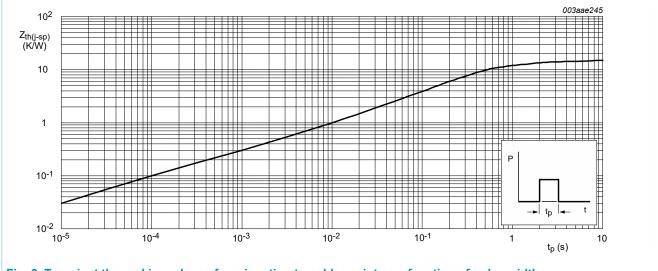
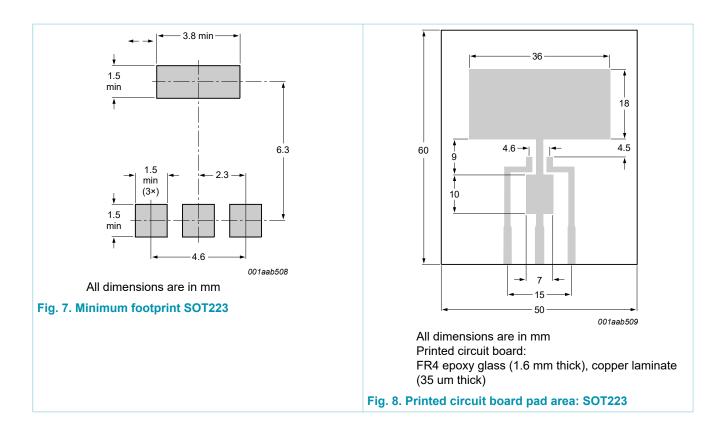


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 9	20	50	200	μΑ
lL	latching current	V_D = 12 V; I_G = 0.5 mA; T_j = 25 °C; $R_{GK(ext)}$ = 1 k Ω ; Fig. 10	-	2	6	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; R_{GK(ext)} = 1 \text{ k}\Omega;$ Fig. 11	-	2	5	mA
V _T	on-state voltage	I _T = 1.2 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.25	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 13	-	0.5	0.8	V
		V _D = 600 V; I _T = 10 mA; T _j = 125 °C	0.2	0.3	-	V
I _D	off-state current	$V_D = 600 \text{ V}; R_{GK(ext)} = 1 \text{ k}\Omega; T_j = 125 °C$	-	0.05	0.1	mA
I _R	reverse current	$V_R = 600 \text{ V}; T_j = 125 \text{ °C}; R_{GK(ext)} = 1 \text{ k}\Omega$	-	0.05	0.1	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GK} = 1 kΩ; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 14	500	800	-	V/µs
		V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	-	25	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 2 A; V_D = 600 V; I_G = 10 mA; $dI_G/$ dt = 0.1 A/µs; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 402 V; T_j = 125 °C; I_{TM} = 1.6 A; V_R = 35 V; $(dI_T/dt)_M$ = 30 A/µs; dV_D/dt = 2 V/µs; $R_{GK(ext)}$ = 1 k Ω ; $(V_{DM}$ = 67% of $V_{DRM})$	-	100	-	μs

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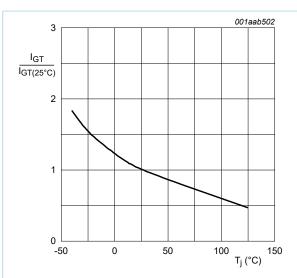


Fig. 9. Normalized gate trigger current as a function of junction temperature

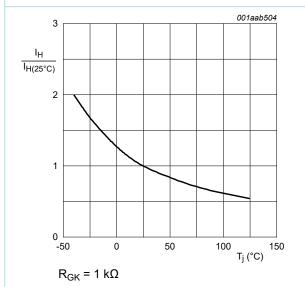


Fig. 11. Normalized holding current as a function of junction temperature

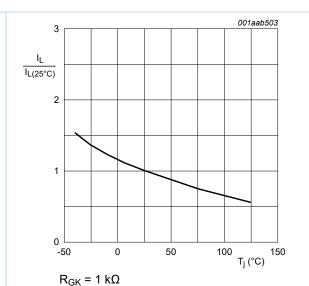
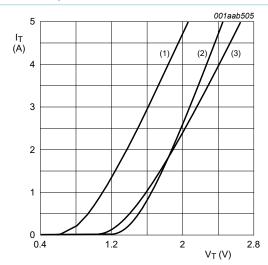


Fig. 10. Normalized latching current as a function of junction temperature



 $V_o = 1.0 \text{ V}; R_s = 0.27 \Omega$

(1) T_i = 125 °C; typical values

(2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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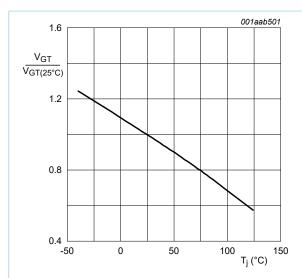


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

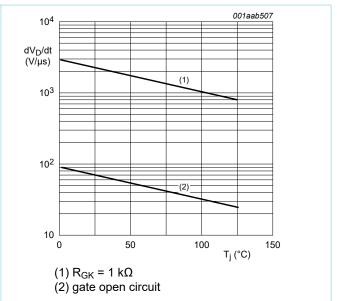


Fig. 14. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

10. Package outline

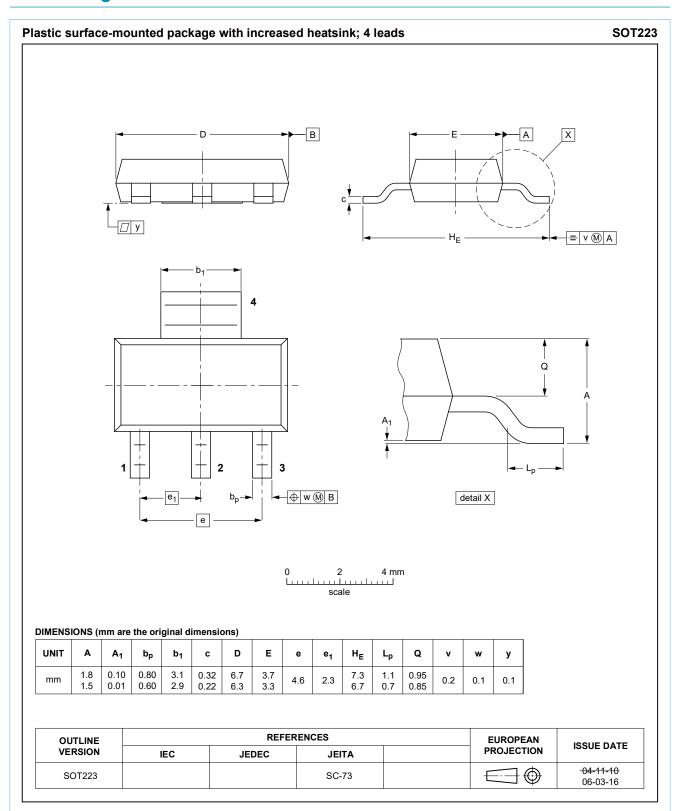
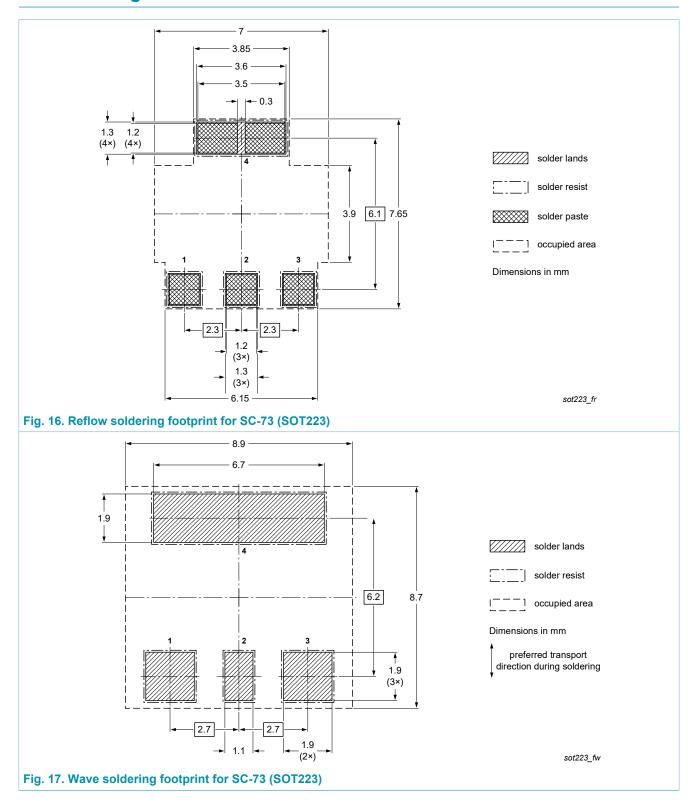


Fig. 15. Package outline SC-73 (SOT223)

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11. Soldering



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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